

CY20AAJ-8H

Nch IGBT for Strobe Flasher

REJ03G0282-0200 Rev.2.00 Nov 29, 2005

Features

V_{CES}: 400 VI_{CM}: 130 A

Drive voltage: 4 VHigh speed switching

Outline

RENESAS Package code: PRSP0008DA-B (Package name: SOP-8 <8P2S-B>)

5,6,7,8

1,2,3 : Emitter 4 : Gate 5,6,7,8 : Collector

Applications

Strobe flasher for cameras

Maximum Ratings

 $(Tc = 25^{\circ}C)$

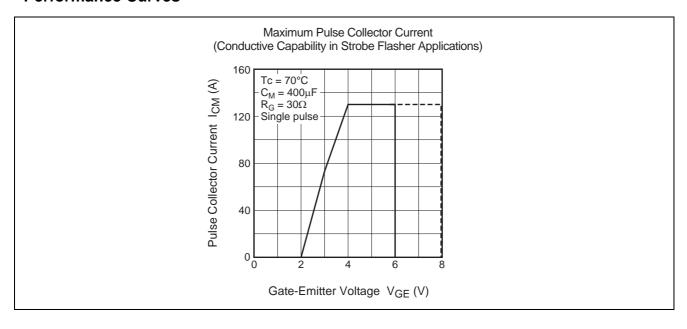
| Parameter | Symbol | Ratings | Unit | Conditions |
|---------------------------|------------------|--------------|------|----------------------------------|
| Collector-emitter voltage | V _{CES} | 400 | V | V _{GE} = 0 V |
| Gate-emitter voltage | V_{GES} | ±6 | V | V _{CE} = 0 V |
| Peak gate-emitter voltage | V_{GEM} | ±8 | V | V _{CE} = 0 V, tw = 10 s |
| Collector current (Pulse) | I _{CM} | 130 | А | $C_{M} = 400 \ \mu F$ |
| | | | | (see performance curve) |
| Junction temperature | Tj | - 40 to +150 | °C | |
| Storage temperature | Tstg | - 40 to +150 | °C | |

Electrical Characteristics

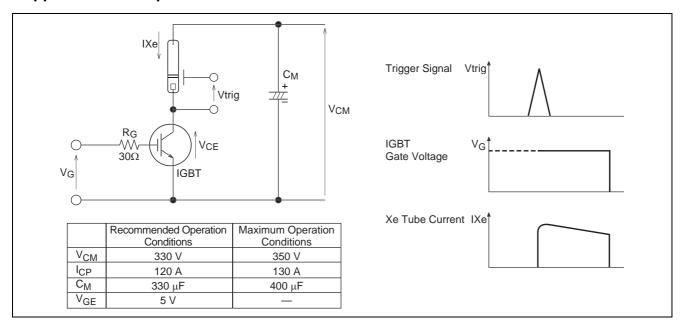
 $(Tch = 25^{\circ}C)$

| Parameter | Symbol | Min. | Тур. | Max. | Unit | Test conditions |
|--------------------------------------|------------------|------|------|------|------|--|
| Collector-emitter breakdown voltage | $V_{(BR)CES}$ | 450 | _ | _ | V | $I_C = 1 \text{ mA}, V_{GE} = 0 \text{ V}$ |
| Collector-emitter leakage current | I _{CES} | _ | _ | 10 | μΑ | $V_{CE} = 400 \text{ V}, V_{GE} = 0 \text{ V}$ |
| Gate-emitter leakage current | I _{GES} | _ | _ | ±10 | μΑ | $V_{GE} = \pm 6 \text{ V}, V_{CE} = 0 \text{ V}$ |
| Gate-emitter threshold voltage | $V_{GE(th)}$ | 0.5 | 0.8 | 1.5 | V | $V_{CE} = 10 \text{ V}, I_{C} = 1 \text{ mA}$ |
| Collector-emitter saturation voltage | $V_{CE(sat)}$ | _ | 4 | 8 | V | $V_{CE} = 4 \text{ V}, I_{C} = 130 \text{ A}$ |
| Fall time | t _f | _ | 0.5 | _ | μs | I _C = 20 A, V _{CC} = 300 V, Resistive loads |
| | | | | | | $V_{GE} = 5 \text{ V}, R_G = 30 \Omega$ |

Performance Curves



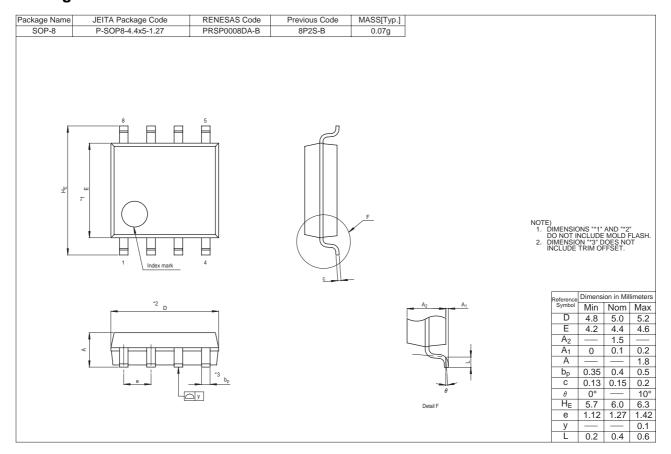
Application Example



Precautions on Usage

- 1. IGBT has MOS structure and its gate is insulated by thin silicon oxide. So please handle carefully to protect the device from electrostatic charge.
- 2. Gate drive voltage during on-period must be applied to satisfy the rating of maximum pulse collector current. And peak reverse gate current during turn-off must become less than 0.1 A. (In general, when $R_{G \text{ (off)}} = 30 \Omega$, it is satisfied.)
- 3. The operation life should be endured 5,000 shots under the charge current ($I_{Xe} \le 130~A$: full luminescence condition) of main capacitor ($C_M = 400~\mu F$) which can endure repeated discharge of 5,000 times. Repetition period under full luminescence condition is over 3 seconds.
- 4. Total operation hours applied to the gate-emitter voltage must be within 5,000 hours when V_{GE} is driven at 6 V.

Package Dimensions



Order Code

| Lead form | Standard packing | Quantity | Standard order code | Standard order code example |
|----------------------|-------------------------|----------|-------------------------------------|-----------------------------|
| Surface-mounted type | Taping | 3000 | Type name – T +Direction (1 or 2)+3 | CY20AAJ-8H-T13 |
| Surface-mounted type | Plastic Magazine (Tube) | 100 | Type name | CY20AAJ-8H |

Note: Please confirm the specification about the shipping in detail.

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